Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/dt 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt 9.0 A/ms minimum at 125°C
- Device Marking: Logo, Device Type, e.g., MAC16D, Date Code

| Rating | Symbol | Value | Unit |
|---|---------------------|----------------|--------------------|
| Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC16D | Vdrm, Vrrm | 400 | Volts |
| MAC16M MAC16N | | 600 800 | |
| On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_{C} = 80^{\circ}C$) | ^I T(RMS) | 16 | Amps |
| Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 125°C) | ITSM | 150 | Amps |
| Circuit Fusing Consideration (t = 8.3 ms) | l ² t | 93 | A ² sec |
| Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C) | PGM | 20 | Watts |
| Average Gate Power (t = 8.3 ms, $T_C = 80^{\circ}C$) | PG(AV) | 0.5 | Watt |
| Operating Junction Temperature Range | Тj | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

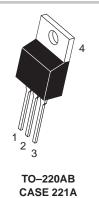


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TRIACS 16 AMPERES RMS 400 thru 800 VOLTS





CASE 221 STYLE 4

| PIN ASSIGNMENT | | |
|----------------|-----------------|--|
| 1 | Main Terminal 1 | |
| 2 | Main Terminal 2 | |
| 3 | Gate | |
| 4 | Main Terminal 2 | |

ORDERING INFORMATION

| Device | Package | Shipping |
|--------|---------|---------------|
| MAC16D | TO220AB | 50 Units/Rail |
| MAC16M | TO220AB | 50 Units/Rail |
| MAC16N | TO220AB | 50 Units/Rail |

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|--|-------------|------|
| Thermal Resistance — Junction to Case — Junction to Ambient | R _θ JC R _θ JA | 2.0 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | тլ | 260 | °C |

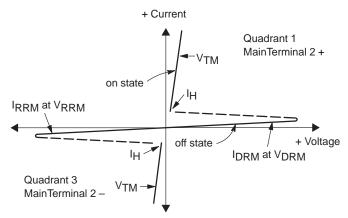
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|--|-------------------|----------------------|-------------------|-------|
| OFF CHARACTERISTICS | 1 | | 1 | | 1 |
| Peak Repetitive Blocking Current $T_J = 25^{\circ}C$ $(V_D = Rated V_{DRM}, V_{RRM}; Gate Open)$ $T_J = 125^{\circ}C$ $T_J = 125^{\circ}C$ | I _{DRM} , I _{RRM} | | | 0.01 2.0 | mA |
| ON CHARACTERISTICS | | | | | |
| Peak On-State Voltage* (I _{TM} = ±21 A Peak) | V _{TM} | _ | 1.2 | 1.6 | Volts |
| Gate Trigger Current (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | IGT | 10 10 10 | 16 18 22 | 50 50 50 | mA |
| Holding Current ($V_D = 12 V$, Gate Open, Initiating Current = ±150 mA) | Ч | _ | 20 | 50 | mA |
| Latching Current ($V_D = 24 V$, $I_G = 50 mA$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | IL | | 33 36 33 | 50 80 50 | mA |
| Gate Trigger Voltage (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) | V _{GT} | 0.5 0.5 0.5 | 0.75 0.72 0.82 | 1.5 1.5 1.5 | Volts |
| DYNAMIC CHARACTERISTICS | | | | | |
| Rate of Change of Commutating Current, See Figure 10. ($V_D = 400 V$, $I_{TM} = 6.0 A$, Commutating dv/dt = 24 V/µs, Gate Open, $T_J = 125^{\circ}C$, f = 250 Hz, No Snubber) $C_L = 10 \mu F$ $L_L = 40 mH$ | (di/dt) _C | 9.0 | _ | _ | A/ms |
| Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Waveform, Gate Open, T_J = 125°C) | dv/dt | 500 | - | - | V/µs |

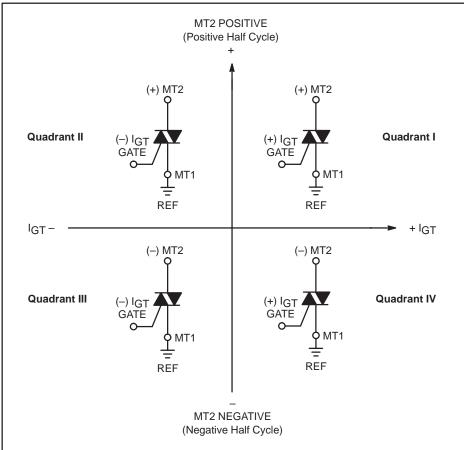
*Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|----------------|---|
| VDRM | Peak Repetitive Forward Off State Voltage |
| IDRM | Peak Forward Blocking Current |
| VRRM | Peak Repetitive Reverse Off State Voltage |
| IRRM | Peak Reverse Blocking Current |
| VTM | Maximum On State Voltage |
| Ι _Η | Holding Current |

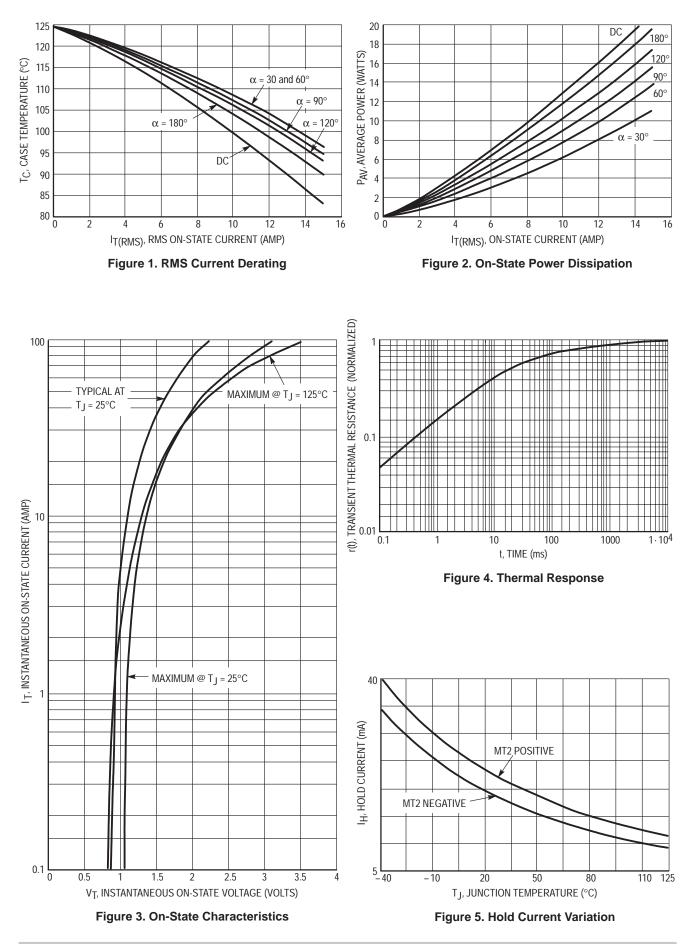


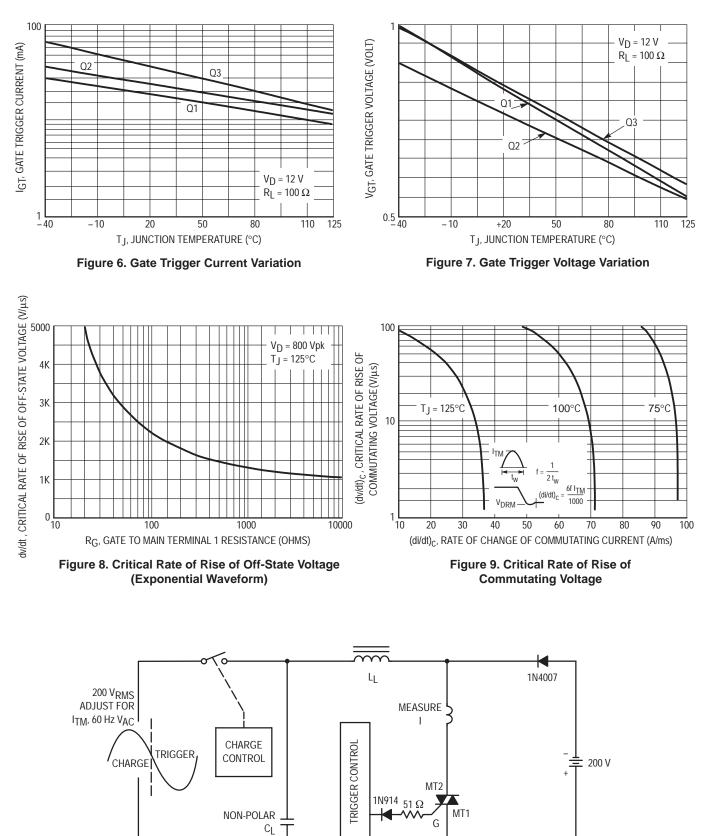




All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



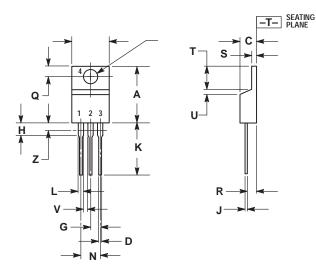


Note: Component values are for verification of rated (di/dt)_C. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 **ISSUE Z**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES | | MILLIN | ILLIMETERS | |
|-----|--------|-------|--------|------------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.570 | 0.620 | 14.48 | 15.75 | |
| В | 0.380 | 0.405 | 9.66 | 10.28 | |
| С | 0.160 | 0.190 | 4.07 | 4.82 | |
| D | 0.025 | 0.035 | 0.64 | 0.88 | |
| F | 0.142 | 0.147 | 3.61 | 3.73 | |
| G | 0.095 | 0.105 | 2.42 | 2.66 | |
| Н | 0.110 | 0.155 | 2.80 | 3.93 | |
| J | 0.018 | 0.025 | 0.46 | 0.64 | |
| К | 0.500 | 0.562 | 12.70 | 14.27 | |
| L | 0.045 | 0.060 | 1.15 | 1.52 | |
| Ν | 0.190 | 0.210 | 4.83 | 5.33 | |
| Q | 0.100 | 0.120 | 2.54 | 3.04 | |
| R | 0.080 | 0.110 | 2.04 | 2.79 | |
| S | 0.045 | 0.055 | 1.15 | 1.39 | |
| Т | 0.235 | 0.255 | 5.97 | 6.47 | |
| U | 0.000 | 0.050 | 0.00 | 1.27 | |
| V | 0.045 | | 1.15 | | |
| Z | | 0.080 | | 2.04 | |

STYLE 4: PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2 3. GATE 4. MAIN TERMINAL 2

Notes

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